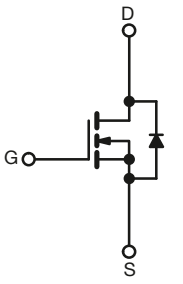
# N-Channel 200 V (D-S) 175 °C MOSFET

| PRODUCT SUMMARY | |
|---|---|
| $V_{DS}$ (V) | 200 |
| $R_{DS(on)}$ Typ. (Ω) at $V_{GS}$ = 10 V | 0.0076 |
| $R_{DS(on)}$ Typ. (Ω) at $V_{GS}$ = 7.5 V | 0.0086 |
| $Q_g$ typ. (nC) | 58 |
| $I_D$ (A) | 100 |
| Configuration | Single |

TO-263


Top View




N-Channel MOSFET

## FEATURES

- ThunderFET® power MOSFET
- Maximum 175 °C junction temperature
- 100 % $R_g$ and UIS tested

RoHS COMPLIANT
HALOGEN FREE

## APPLICATIONS

- Power supplies:
  - Uninterruptible power supplies
  - AC/DC switch-mode power supplies
  - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Solar micro inverter
- Class D audio amplifier

| ABSOLUTE MAXIMUM RATINGS ($T_A$ = 25 °C, unless otherwise noted) | | | | |
|---|---|---|---|---|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Drain-source voltage | | $V_{DS}$ | 200 | V |
| Gate-source voltage | | $V_{GS}$ | ± 20 | |
| Continuous drain current | $T_C$ = 25 °C | $I_D$ | 100 | A |
| | $T_C$ = 125 °C | | 62 | |
| Pulsed drain current (t = 100 µs) | | $I_{DM}$ | 300 | |
| Continuous source-drain diode current | | $I_S$ | 100 | |
| Single pulse avalanche current [a] | L = 0.1 mH | $I_{AS}$ | 60 | |
| Single pulse avalanche energy [a] | | $E_{AS}$ | 180 | mJ |
| Maximum power dissipation | $T_C$ = 25 °C | $P_D$ | 375 [b] | W |
| | $T_C$ = 125 °C | | 125 [b] | |
| Operating junction and storage temperature range | | $T_J$, $T_{stg}$ | -55 to +175 | °C |
| Soldering recommendations (peak temperature) [c] | | | 260 | |

| THERMAL RESISTANCE RATINGS | | | | |
|---|---|---|---|---|
| PARAMETER | | SYMBOL | MAXIMUM | UNIT |
| Maximum junction-to-ambient (PCB mount) [c] | | $R_{thJA}$ | 40 | °C/W |
| Maximum junction-to-case (drain) | Steady state | $R_{thJC}$ | 0.4 | |

**Notes**

a. Duty cycle ≤ 1 %.
b. See SOA curve for voltage derating.
c. When mounted on 1" square PCB (FR4 material).
d. Package limited.

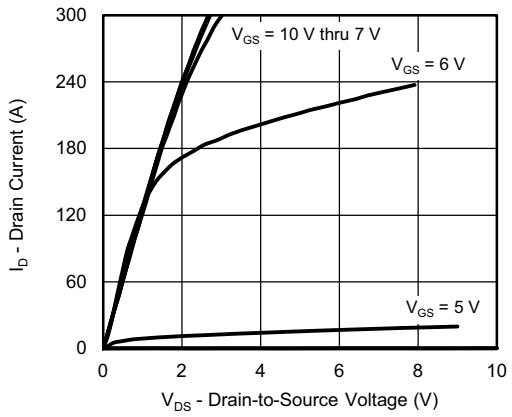
| **SPECIFICATIONS** ($T_J$ = 25 °C, unless otherwise noted) | | | | | | |
|---|---|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | **MIN.** | **TYP.** | **MAX.** | **UNIT** |
| **Static** | | | | | | |
| Drain-source breakdown voltage | $V_{DS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 µA | 200 | - | - | V |
| Gate-source threshold voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$ , $I_D$ = 250 µA | 2 | - | 4 | V |
| Gate-source leakage | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ± 20 V | - | - | 250 | nA |
| Zero gate voltage drain current | $I_{DSS}$ | $V_{DS}$ = 200 V, $V_{GS}$ = 0 V | - | - | 1 | µA |
| | | $V_{DS}$ = 200 V, $V_{GS}$ = 0 V, $T_J$ = 125 °C | - | - | 150 | |
| | | $V_{DS}$ = 200 V, $V_{GS}$ = 0 V, $T_J$ = 175 °C | - | - | 5 | mA |
| On-state drain current [a] | $I_{D(on)}$ | $V_{DS}$ ≥ 10 V, $V_{GS}$ = 10 V | 60 | - | - | A |
| Drain-source on-state resistance [a] | $R_{DS(on)}$ | $V_{GS}$ = 10 V, $I_D$ = 40 A | - | 0.0076 | - | Ω |
| | | $V_{GS}$ = 7.5 V, $I_D$ = 40 A | - | 0.0086 | - | |
| Forward transconductance [a] | $g_{fs}$ | $V_{DS}$ = 15 V, $I_D$ = 40 A | - | 63 | - | S |
| **Dynamic [b]** | | | | | | |
| Input capacitance | $C_{iss}$ | $V_{DS}$ = 100 V, $V_{GS}$ = 0 V, f = 1 MHz | - | 3120 | - | pF |
| Output capacitance | $C_{oss}$ | | - | 280 | - | |
| Reverse transfer capacitance | $C_{rss}$ | | - | 24 | - | |
| Total gate charge | $Q_g$ | $V_{DS}$ = 100 V, $V_{GS}$ = 10 V, $I_D$ = 60 A | - | 58 | 87 | nC |
| Gate-source charge | $Q_{gs}$ | | - | 17.6 | - | |
| Gate-drain charge | $Q_{gd}$ | | - | 17.2 | - | |
| Output charge | $Q_{oss}$ | $V_{DS}$ = 100 V, $V_{GS}$ = 0 V | - | 108 | 162 | |
| Gate resistance | $R_g$ | f = 1 MHz | 1.5 | 3 | 5 | Ω |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}$ = 100 V, $R_L$ = 1.66 Ω, $I_D$ ≅ 60 A, $V_{GEN}$ = 10 V, $R_g$ = 1 Ω | - | 14 | 28 | ns |
| Rise time | $t_r$ | | - | 125 | 250 | |
| Turn-off delay time | $t_{d(off)}$ | | - | 27 | 54 | |
| Fall time | $t_f$ | | - | 80 | 150 | |
| **Drain-Source Body Diode Characteristics** | | | | | | |
| Pulse diode forward current (t = 100 µs) | $I_{SM}$ | | - | - | 240 | A |
| Body diode voltage | $V_{SD}$ | $I_F$ = 30 A, $V_{GS}$ = 0 V | - | 0.85 | 1.5 | V |
| Body diode reverse recovery time | $t_{rr}$ | $I_F$ = 30 A, dI/dt = 100 A/µs | - | 150 | 300 | ns |
| Body diode reverse recovery charge | $Q_{rr}$ | | - | 0.9 | 1.8 | nC |
| Reverse recovery fall time | $t_a$ | | - | 125 | - | ns |
| Reverse recovery rise time | $t_b$ | | - | 25 | - | |
| Body diode peak reverse recovery charge | $I_{RM(REC)}$ | | - | 11.5 | 20 | A |

**Notes**

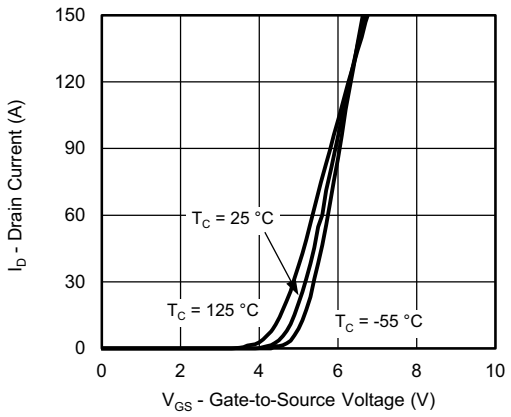
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

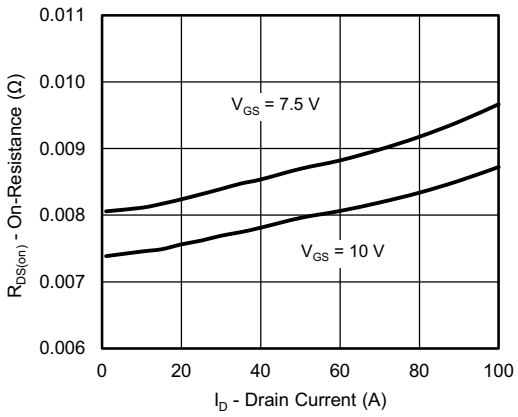
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



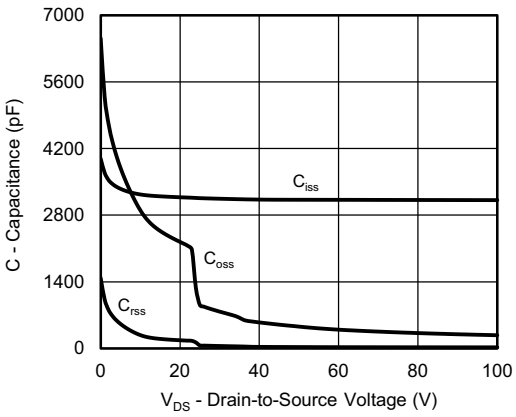

**Output Characteristics**



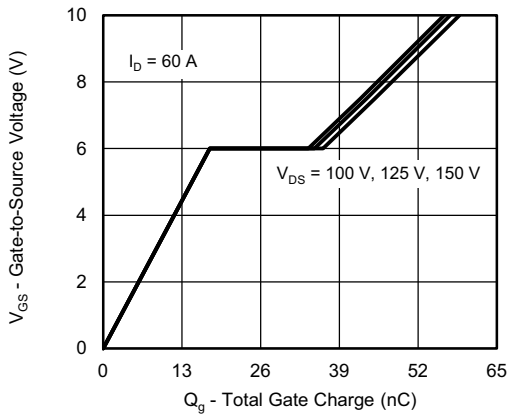

**Transfer Characteristics**



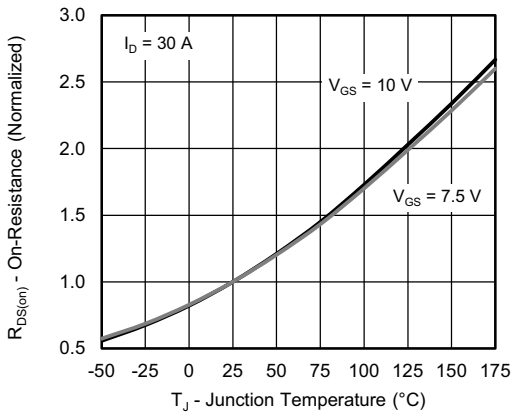

**On-Resistance vs. Drain Current and Gate Voltage**




**Capacitance**

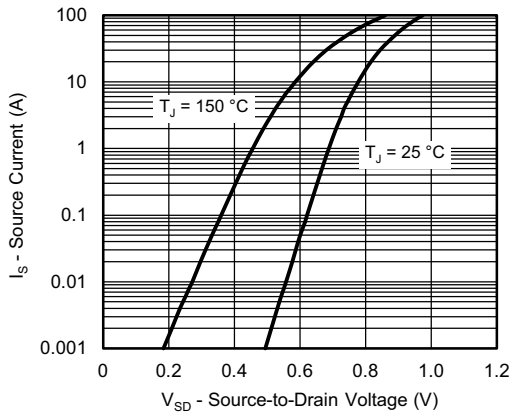



**Gate Charge**

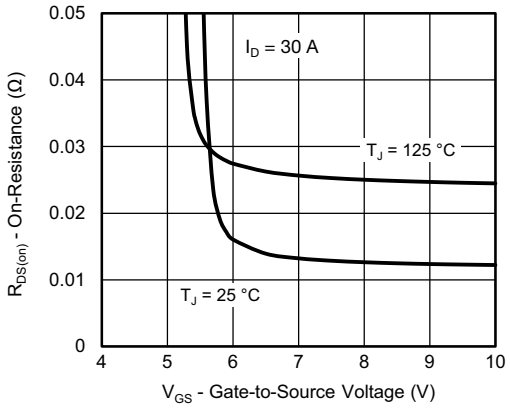



**On-Resistance vs. Junction Temperature**

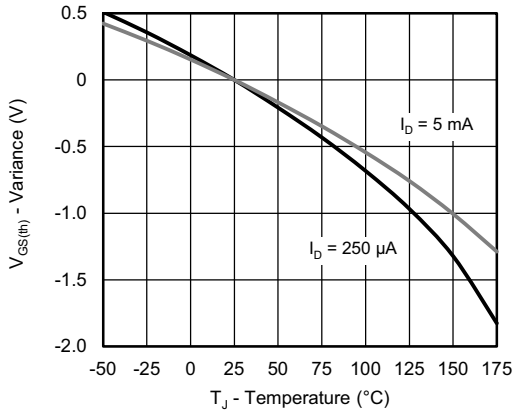
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



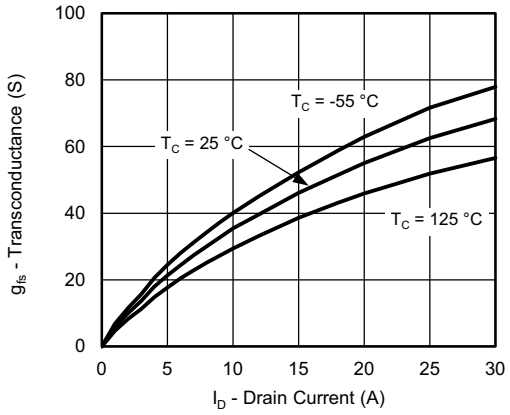

**Source-Drain Diode Forward Voltage**



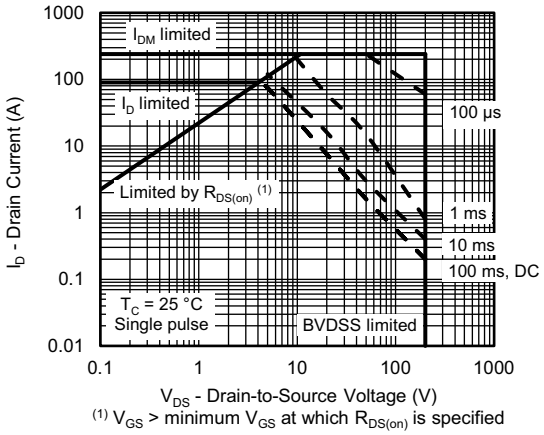

**On-Resistance vs. Gate-to-Source Voltage**




**Threshold Voltage**

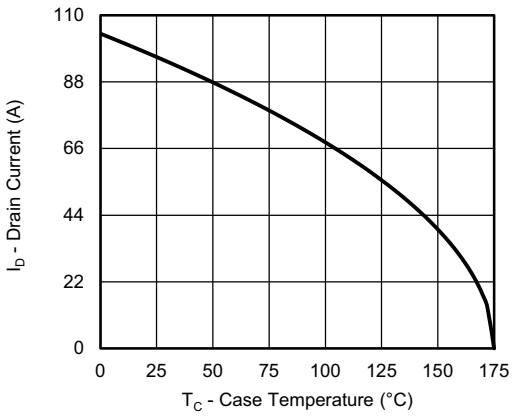



**Transconductance**

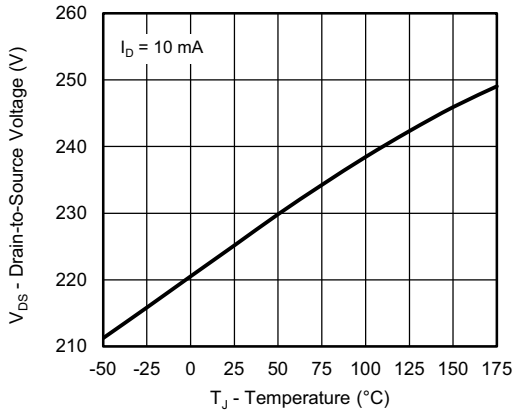



**Safe Operating Area, Junction-to-Ambient**

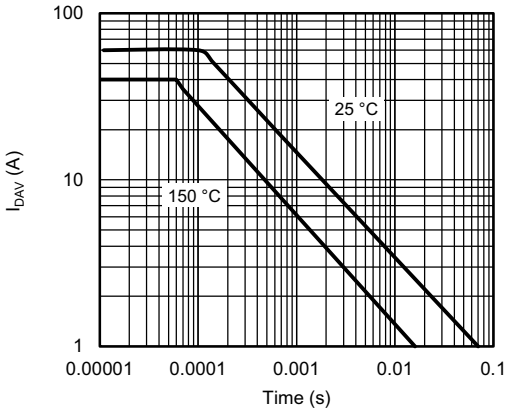
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)




**Current Derating [a]**




**Drain Source Breakdown vs. Junction Temperature**

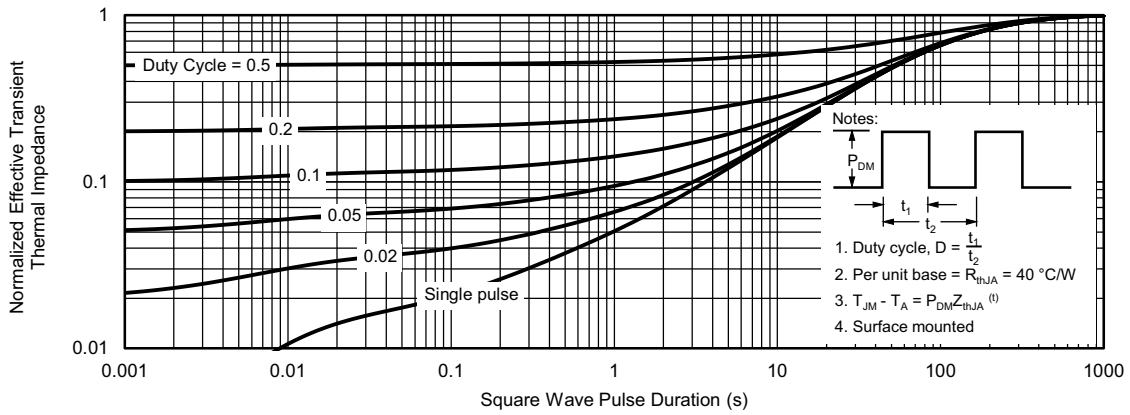



**$I_{DAV}$ vs. Time**

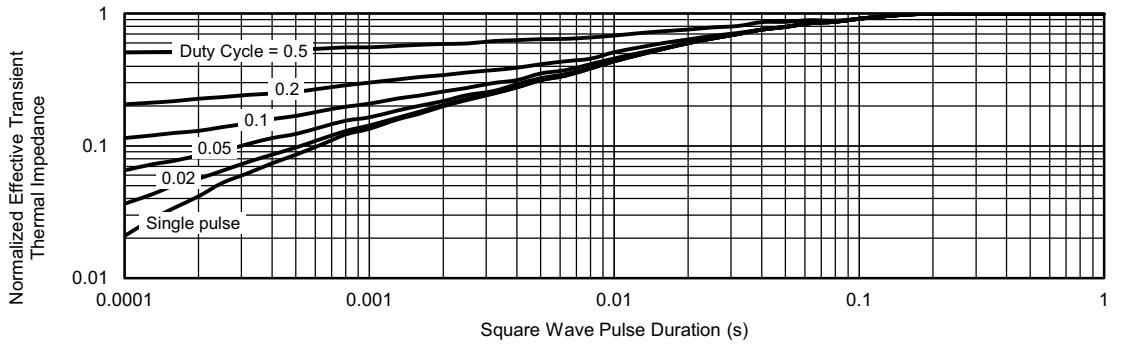
**Note**

a. The power dissipation $P_D$ is based on $T_J$ max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)




**Normalized Thermal Transient Impedance, Junction-to-Ambient**




**Normalized Thermal Transient Impedance, Junction-to-Case**

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